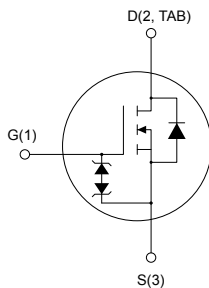
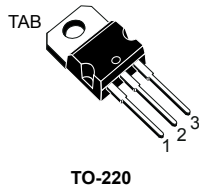


## N-channel 800 V, 750 mΩ typ., 6 A MDmesh K6 Power MOSFET in a TO-220 package



AM01476v1\_tab



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STP80N900K6	800 V	900 mΩ	6 A

- Worldwide best R<sub>DS(on)</sub> x area
- Worldwide best FOM (figure of merit)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

### Applications

- Flyback converter
- Adapters for tablets, notebook and AIO
- LED lighting

### Description

This very high voltage N-channel Power MOSFET is designed using the ultimate MDmesh K6 technology based on 20 years STMicroelectronics experience on super junction technology. The result is the best-in-class on-resistance per area and gate charge for applications requiring superior power density and high efficiency.

#### Product status link

[STP80N900K6](#)

#### Product summary

<b>Order code</b>	STP80N900K6
<b>Marking</b>	80N900K6
<b>Package</b>	TO-220
<b>Packing</b>	Tube

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	6	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4	
$I_{DM}^{(1)}$	Drain current (pulsed)	11	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	68	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	5	V/ns
$di/dt^{(2)}$	Peak diode recovery current slope	100	A/ $\mu\text{s}$
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	120	V/ns
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range		$^\circ\text{C}$

1. Pulse width limited by safe operating area.

2.  $I_{SD} \leq 3\text{ A}$ ;  $V_{DS}(\text{peak}) = 400\text{ V}$ .

3.  $V_{DS} \leq 640\text{ V}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance, junction-to-case	1.83	$^\circ\text{C/W}$
$R_{thJA}$	Thermal resistance, junction-to-ambient	62.5	$^\circ\text{C/W}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_J$ max.)	1.8	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	65	mJ

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified.

**Table 4. On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	800			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$ , $T_C = 125\text{ }^\circ\text{C}^{(1)}$			50	
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 1$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3.0	3.5	4.0	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$		750	900	m $\Omega$

1. Specified by design, not tested in production.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 400\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	362	-	pF
$C_{oss}$	Output capacitance		-	6.2	-	pF
$C_{o(er)}^{(1)}$	Equivalent capacitance energy related	$V_{DS} = 0\text{ to }640\text{ V}$ , $V_{GS} = 0\text{ V}$	-	9	-	pF
$C_{o(tr)}^{(2)}$	Equivalent capacitance time related		-	46	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	3.6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 640\text{ V}$ , $I_D = 3\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 18. Test circuit for gate charge behavior)	-	7	-	nC
$Q_{gs}$	Gate-source charge		-	2	-	nC
$Q_{gd}$	Gate-drain charge		-	2.4	-	nC

1.  $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to the stated value.

2.  $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to the stated value.

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$ , $I_D = 3\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$	-	8.1	-	ns
$t_r$	Rise time		-	5.4	-	ns
$t_{d(off)}$	Turn-off delay time	see (Figure 16. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	23.8	-	ns
$t_f$	Fall time		-	13	-	ns

**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		11	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 6\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,	-	229		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$	-	2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 19. Test circuit for inductive load switching and diode recovery times)	-	13.7		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,	-	365		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	-	2.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 19. Test circuit for inductive load switching and diode recovery times)	-	11.8		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

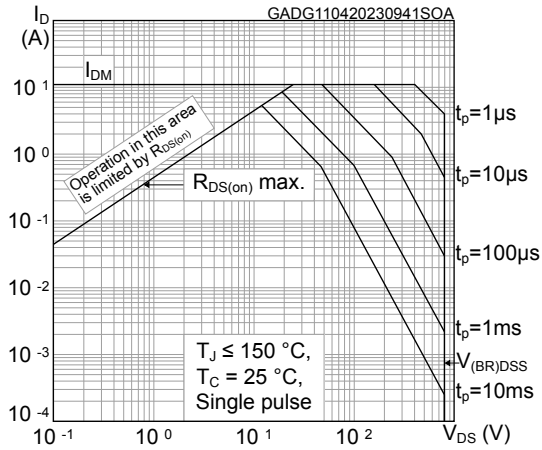


Figure 2. Maximum transient thermal impedance

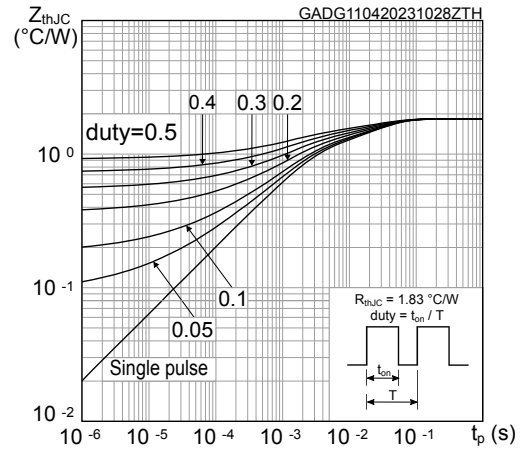


Figure 3. Typical output characteristics

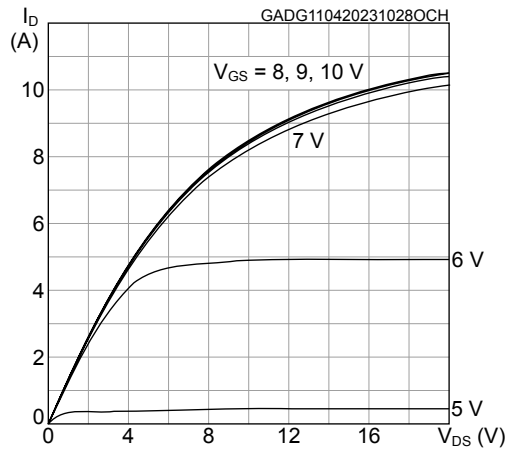


Figure 4. Typical transfer characteristics

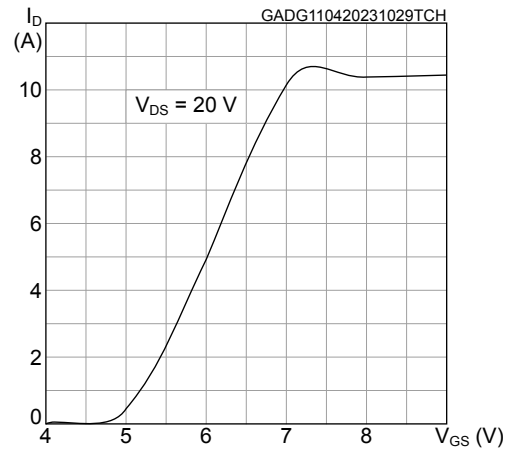


Figure 5. Typical drain-source on-resistance

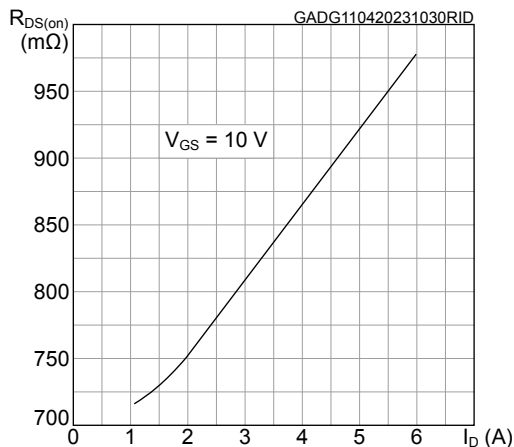
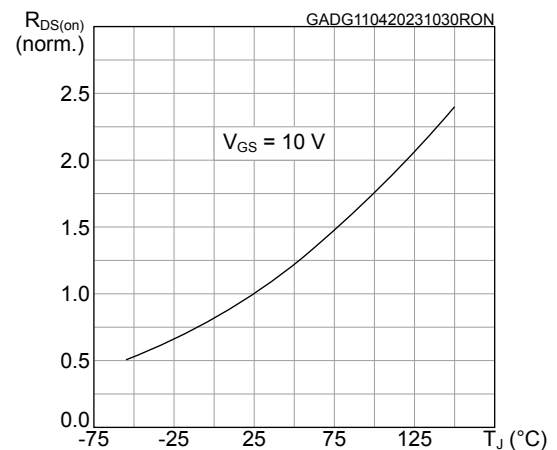
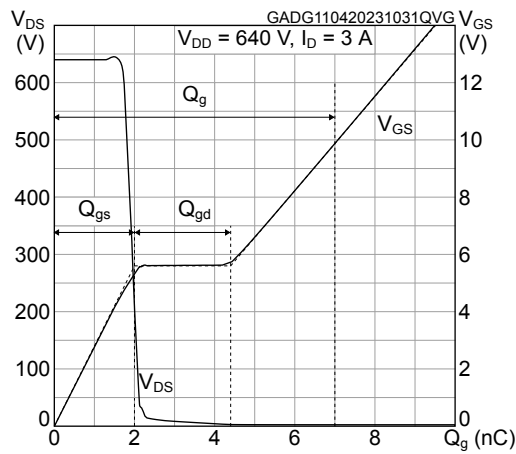


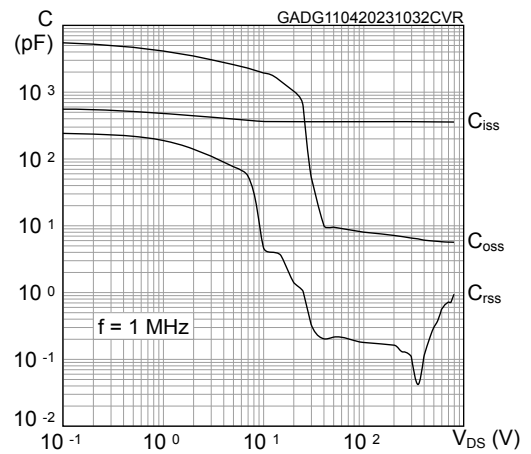
Figure 6. Normalized on-resistance vs temperature



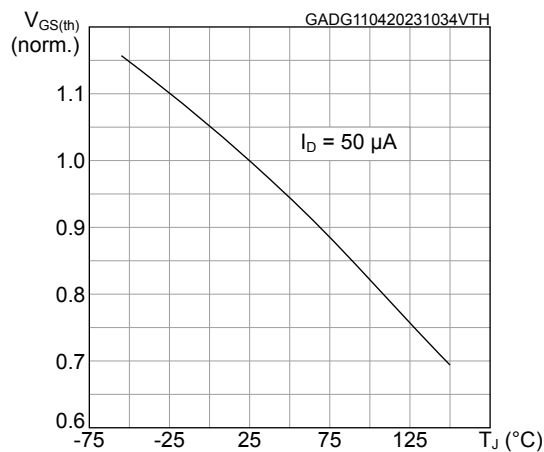
**Figure 7. Typical gate charge characteristics**



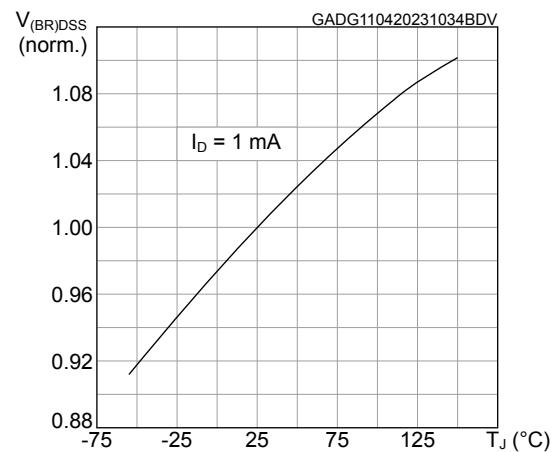
**Figure 8. Typical capacitance characteristics**



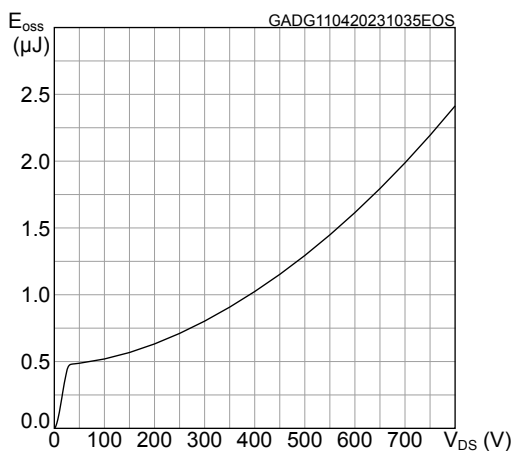
**Figure 9. Normalized gate threshold vs temperature**



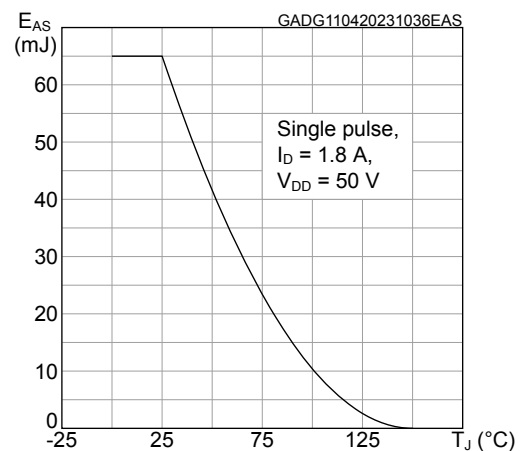
**Figure 10. Normalized breakdown voltage vs temperature**



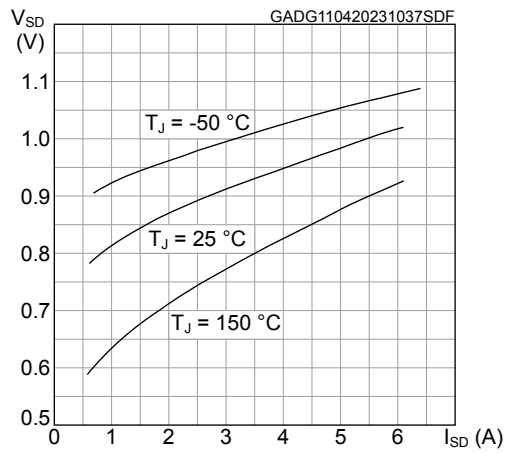
**Figure 11. Typical output capacitance stored energy**



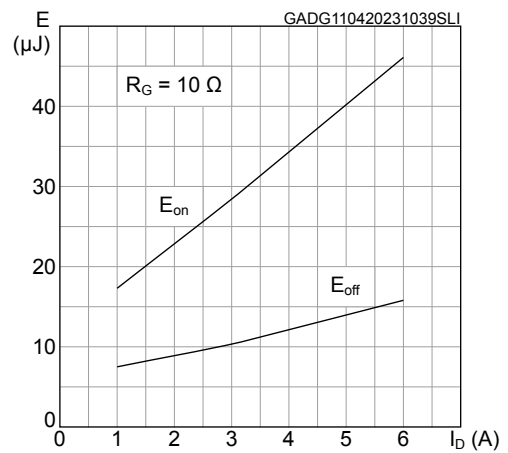
**Figure 12. Maximum avalanche energy vs temperature**



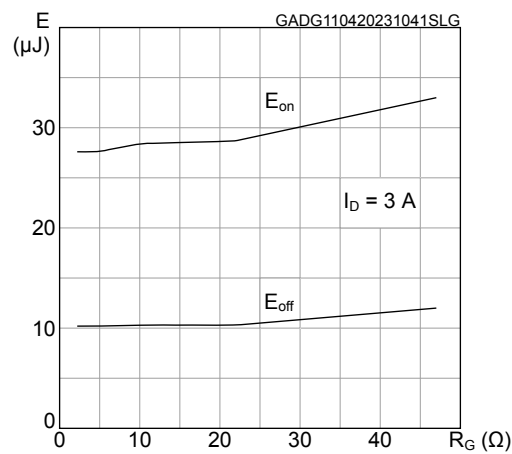
**Figure 13. Typical reverse diode forward characteristics**



**Figure 14. Typical inductive load switching energy vs  $I_D$**

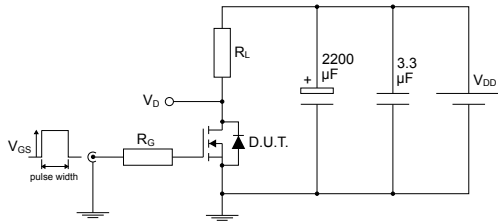


**Figure 15. Typical inductive load switching energy vs  $R_G$**



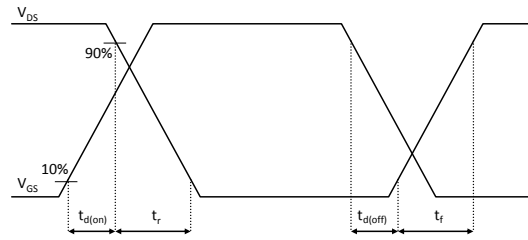
### 3 Test circuits

Figure 16. Test circuit for resistive load switching times



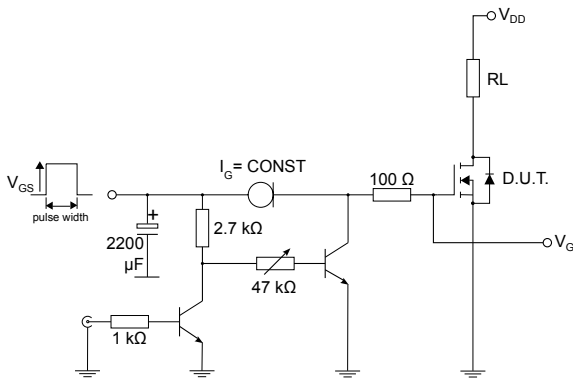
AM01468v1

Figure 17. Switching time waveform



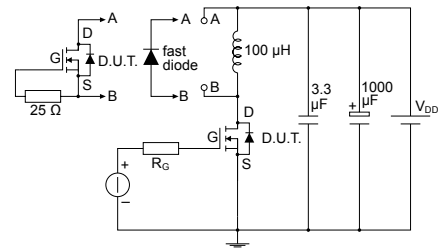
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Figure 18. Test circuit for gate charge behavior



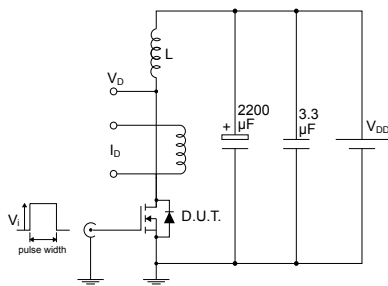
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Figure 19. Test circuit for inductive load switching and diode recovery times



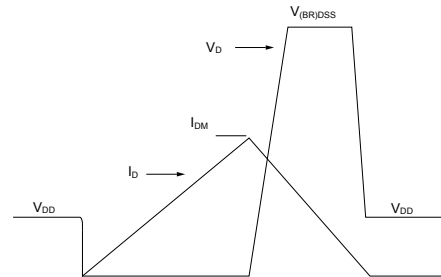
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Figure 20. Unclamped inductive load test circuit



AM01471v1

Figure 21. Unclamped inductive waveform



AM01472v1

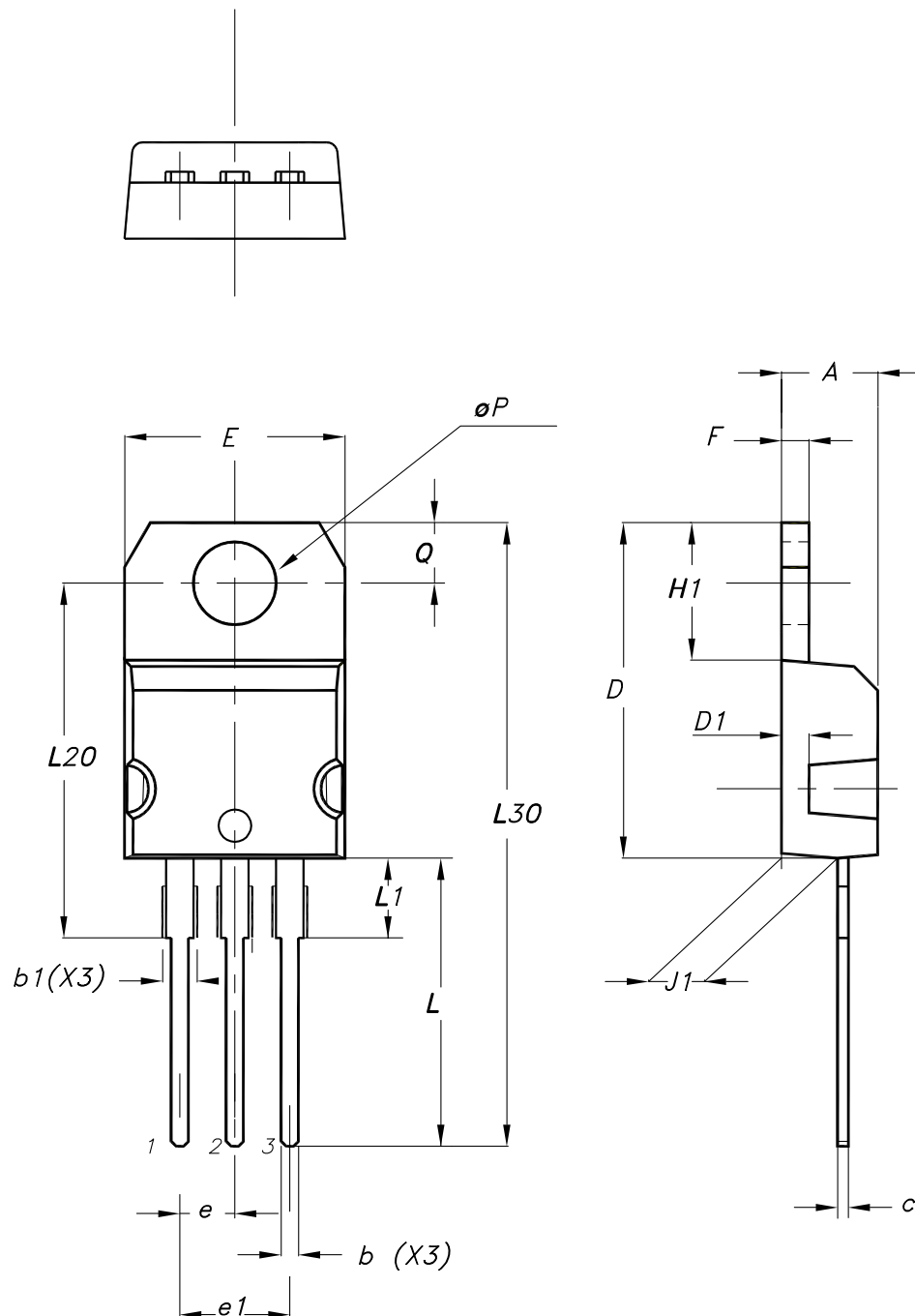


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-220 type A package information

Figure 22. TO-220 type A package outline



0015988\_typeA\_Rev\_23

**Table 8. TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
13-Apr-2023	1	First release.

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